



## N-channel Enhancement Mode Mosfet

CX3075

### DESCRIPTION

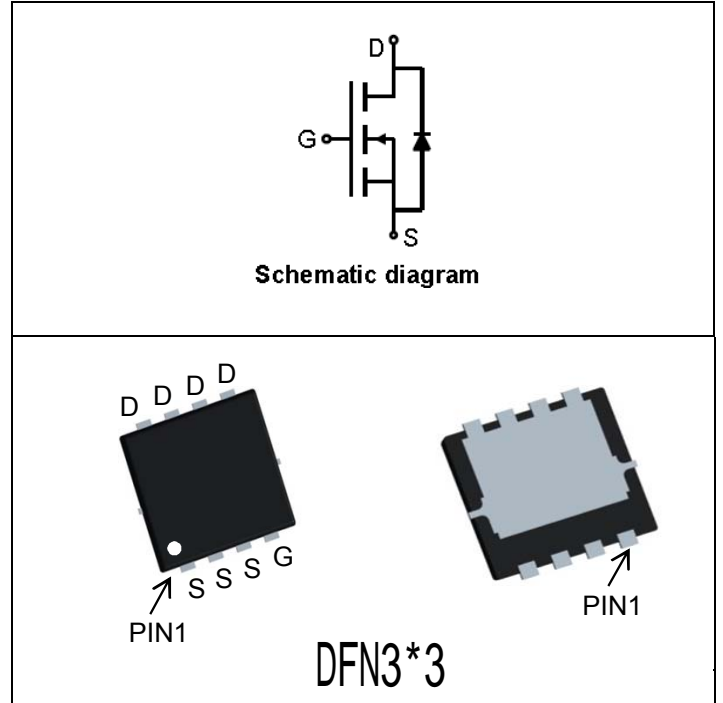
The CX3075 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

### GENERAL FEATURES

- RDS(ON) < 8mΩ @ VGS=4.5V  
RDS(ON) < 5mΩ @ VGS=10V
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

### Application

- PWM applications
- Load switch
- Power management



### ■ Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V <sub>DS</sub>	30	V
Gate-source Voltage		V <sub>GS</sub>	±20	V
Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	30	A
	T <sub>C</sub> =100°C		21	
Pulsed Drain Current <sup>A</sup>		I <sub>DM</sub>	120	A
Total Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	35	W
	T <sub>C</sub> =100°C		15	W
Single Pulse Avalanche Energy <sup>B</sup>		E <sub>AS</sub>	29	mJ
Thermal Resistance Junction-to-Case <sup>C</sup>		R <sub>θJC</sub>	3.4	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55~+150	°C